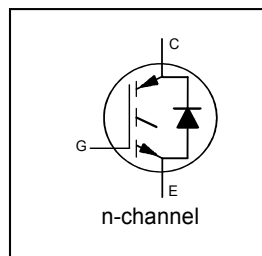
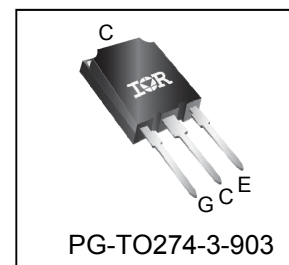


INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE
Features

- Low $V_{CE(on)}$ Trench IGBT Technology
- Low Switching Losses
- 6 μ s SCSOA
- Square RBSOA
- 100% of the parts tested for I_{LM} ①
- Positive $V_{CE(on)}$ Temperature Coefficient
- Soft Recovery Co-pak Diode
- Lead-Free, RoHS Compliant
- Automotive Qualified *



$V_{CES} = 600V$
 $I_C = 160A, T_C = 100^\circ C$
 $t_{sc} \geq 6\mu s, T_{J(MAX)} = 175^\circ C$
 $V_{CE(on) typ.} = 1.70V$



G	C	E
Gate	Collector	Emitter

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGPS4070D0	PG-TO274-3-903	Tube	25	AUIRGPS4070D0

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	240⑤	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	160	
$I_{NOMINAL}$	Nominal Current	120	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$	360	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	480	
$I_{F NOMINAL}$	Diode Nominal Current ②	120⑤	V
I_{FM}	Diode Maximum Forward Current ②	480	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	W
	Transient Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	750	°C
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	375	
T_J	Operating Junction and	-55 to +175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (each IGBT) ④	—	0.20	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case (each Diode) ④	—	0.45	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	

* Qualification standards can be found at www.infineon.com

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0\text{V}$, $I_C = 500\mu\text{A}$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.74	—	V/°C	$V_{GE} = 0\text{V}$, $I_C = 5\text{mA}$ (25°C-175°C)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 120\text{A}$, $V_{GE} = 15\text{V}$, $T_J = 25^\circ\text{C}$
		—	2.0	—		$I_C = 120\text{A}$, $V_{GE} = 15\text{V}$, $T_J = 150^\circ\text{C}$
		—	2.1	—		$I_C = 120\text{A}$, $V_{GE} = 15\text{V}$, $T_J = 175^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	$V_{CE} = V_{GE}$, $I_C = 5.6\text{mA}$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-16	—	mV/°C	$V_{CE} = V_{GE}$, $I_C = 5.6\text{mA}$ (25°C-175°C)
g_{fe}	Forward Transconductance	—	87	—	S	$V_{CE} = 50\text{V}$, $I_C = 120\text{A}$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	200	μA	$V_{GE} = 0\text{V}$, $V_{CE} = 600\text{V}$
		—	2.0	—	mA	$V_{GE} = 0\text{V}$, $V_{CE} = 600\text{V}$, $T_J = 175^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.8	2.1	V	$I_F = 120\text{A}$
		—	1.9	—		$I_F = 120\text{A}$, $T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	$V_{GE} = \pm 20\text{V}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	250	375	nC	$I_C = 120\text{A}$ $V_{GE} = 15\text{V}$ $V_{CC} = 400\text{V}$
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	65	98		
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	100	150		
E_{on}	Turn-On Switching Loss	—	5.7	6.7	mJ	$I_C = 120\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$ $R_G = 4.7\Omega$, $L = 87\mu\text{H}$, $T_J = 25^\circ\text{C}$ Energy losses include tail & diode reverse recovery
E_{off}	Turn-Off Switching Loss	—	4.2	5.2		
E_{total}	Total Switching Loss	—	9.9	11.9		
$t_{d(on)}$	Turn-On delay time	—	40	60	ns	$I_C = 120\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$ $R_G = 4.7\Omega$, $L = 87\mu\text{H}$, $T_J = 25^\circ\text{C}$ Energy losses include tail & diode reverse recovery
t_r	Rise time	—	125	155		
$t_{d(off)}$	Turn-Off delay time	—	140	170		
t_f	Fall time	—	120	170	ns	$I_C = 120\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$ $R_G = 4.7\Omega$, $L = 87\mu\text{H}$, $T_J = 175^\circ\text{C}$ Energy losses include tail & diode reverse recovery
E_{on}	Turn-On Switching Loss	—	6.4	—		
E_{off}	Turn-Off Switching Loss	—	4.7	—		
E_{total}	Total Switching Loss	—	11.1	—	mJ	$I_C = 120\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$ $R_G = 4.7\Omega$, $L = 87\mu\text{H}$, $T_J = 175^\circ\text{C}$ Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	40	—		
t_r	Rise time	—	110	—		
$t_{d(off)}$	Turn-Off delay time	—	160	—	ns	$I_C = 120\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$ $R_G = 4.7\Omega$, $L = 87\mu\text{H}$, $T_J = 175^\circ\text{C}$ Energy losses include tail & diode reverse recovery
t_f	Fall time	—	125	—		
C_{ies}	Input Capacitance	—	7600	—		
C_{oes}	Output Capacitance	—	510	—	pF	$V_{GE} = 0\text{V}$ $V_{CC} = 30\text{V}$ $f = 1.0\text{MHz}$
C_{res}	Reverse Transfer Capacitance	—	230	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}$, $I_C = 480\text{A}$ $V_{CC} = 480\text{V}$, $V_p \leq 600\text{V}$ $R_g = 4.7\Omega$, $V_{GE} = +20\text{V}$ to 0V
SCSOA	Short Circuit Safe Operating Area	6	—	—	μs	$V_{CC} = 400\text{V}$, $V_p \leq 600\text{V}$ $R_g = 5.0\Omega$, $V_{GE} = +15\text{V}$ to 0V
E_{rec}	Reverse Recovery Energy of the Diode	—	1740	—	μJ	$T_J = 175^\circ\text{C}$
t_{rr}	Diode Reverse Recovery Time	—	210	—	ns	$V_{CC} = 400\text{V}$, $I_F = 120\text{A}$
I_{rr}	Peak Reverse Recovery Current	—	45	—	A	$V_{GE} = 15\text{V}$, $R_g = 4.7\Omega$, $L = 87\mu\text{H}$

Notes:

- ① $V_{CC} = 80\%$ (V_{CES}), $V_{GE} = 20\text{V}$, $L = 3.5\mu\text{H}$, $R_G = 47\Omega$ tested in production $ILM \leq 400\text{A}$.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ R_θ is measured at T_J approximately 90°C .
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package IGBT current limit is 195A. Package diode current limit is 120A. Note that current limitations arising from heating of the device leads may occur.

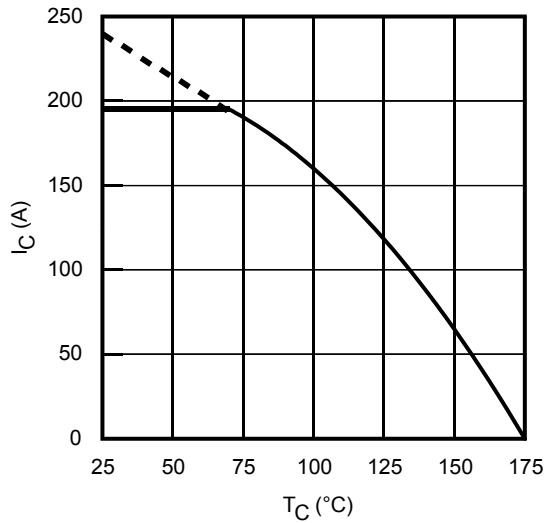


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

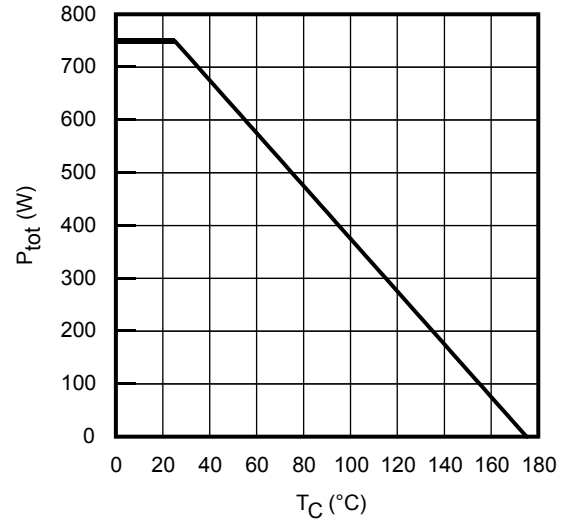


Fig. 2 - Power Dissipation vs. Case Temperature

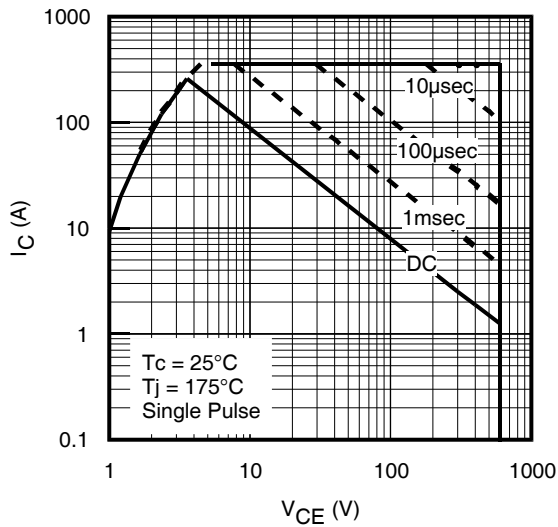


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

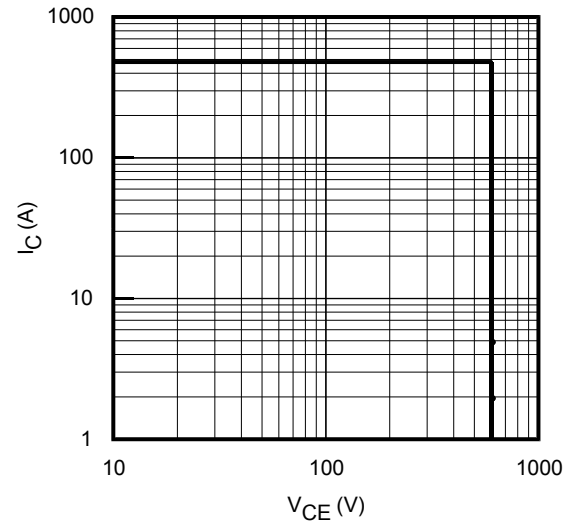


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 20\text{V}$

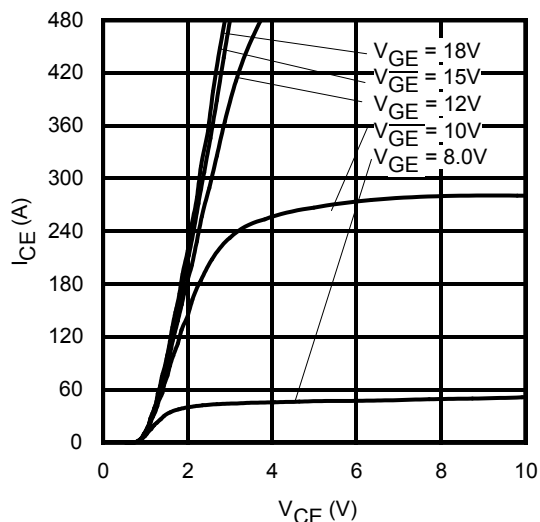


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 20\mu\text{s}$

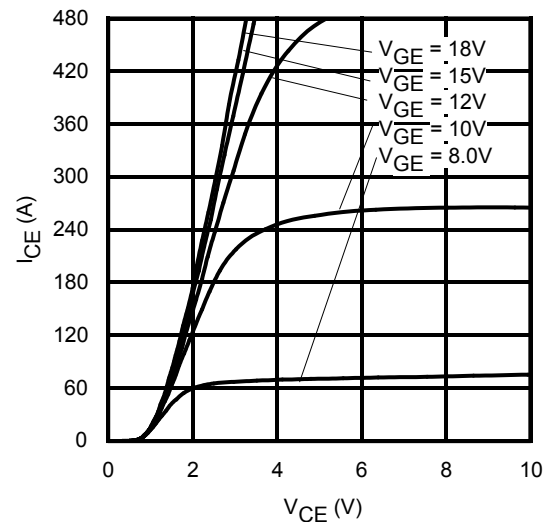


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 20\mu\text{s}$

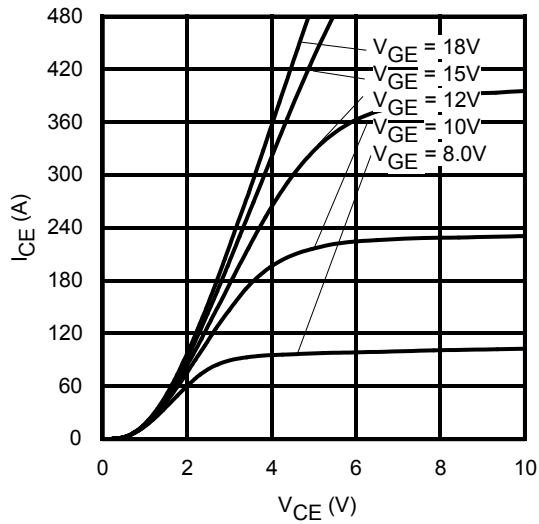


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = 20\mu\text{s}$

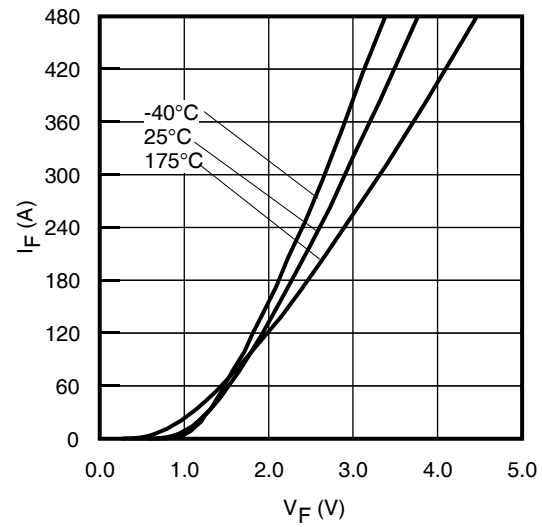


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 20\mu\text{s}$

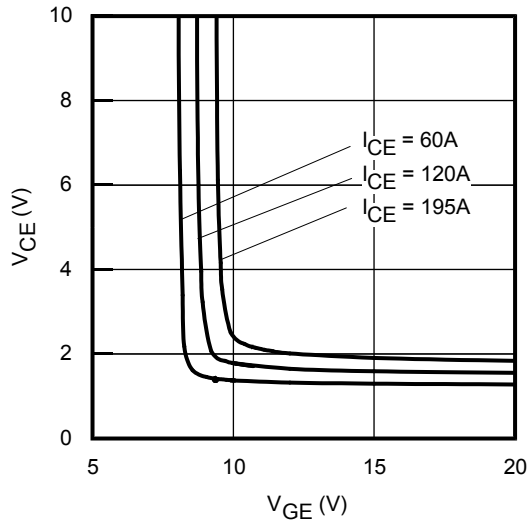


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

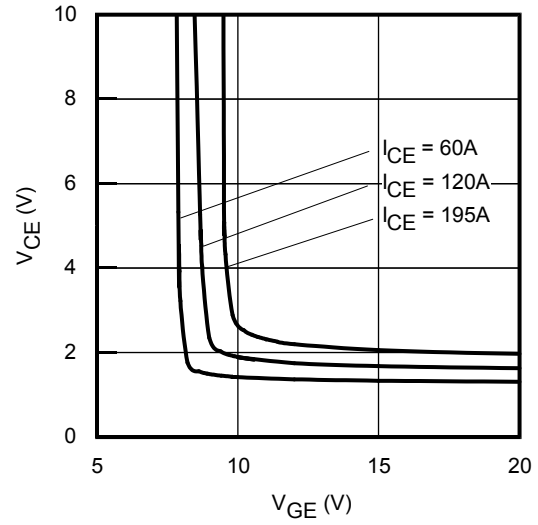


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

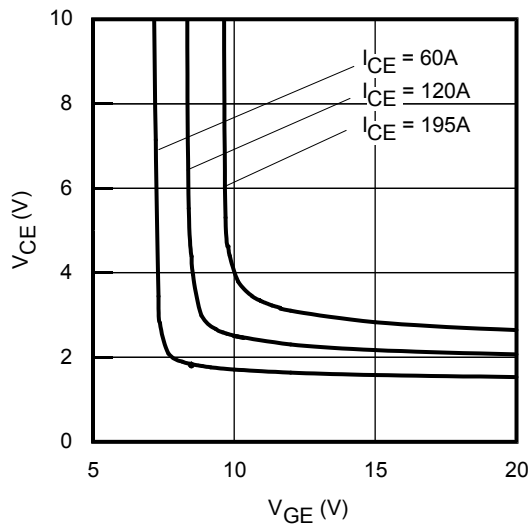


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

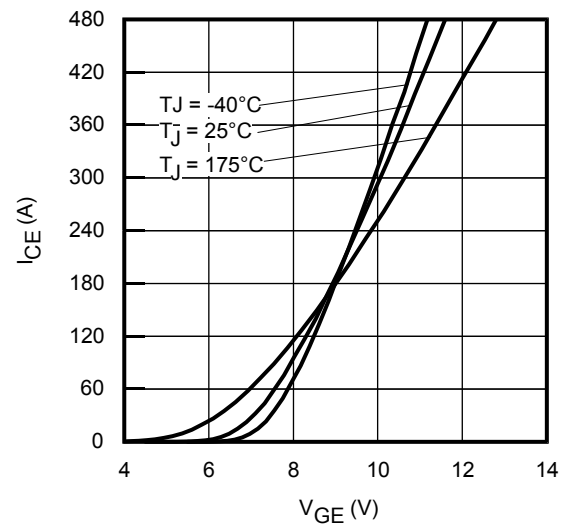
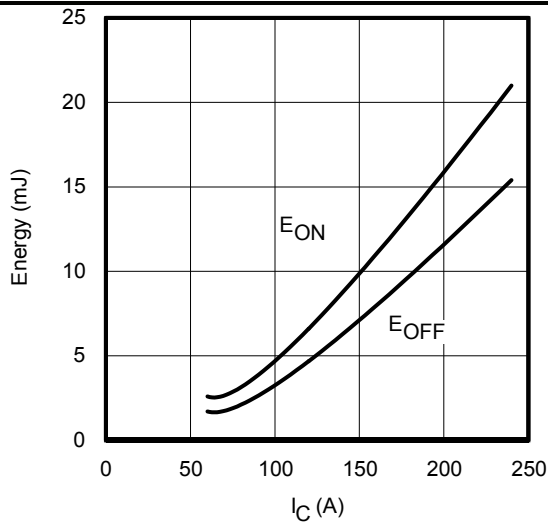
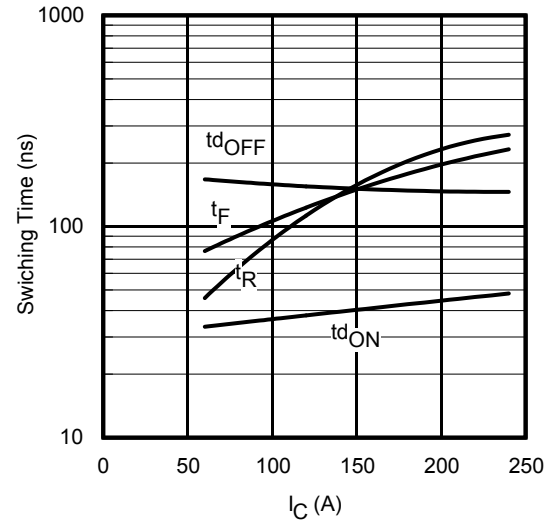
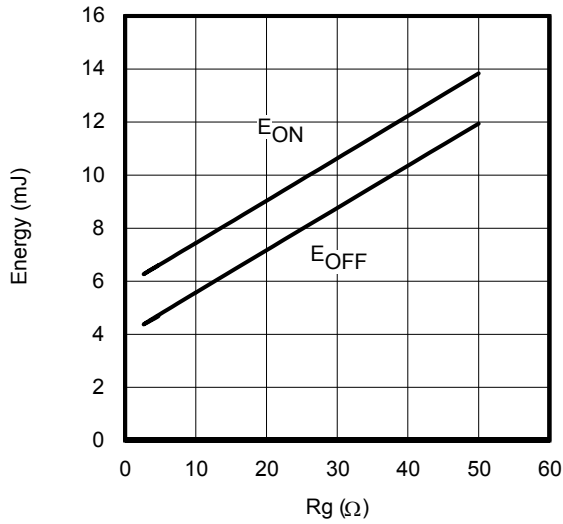
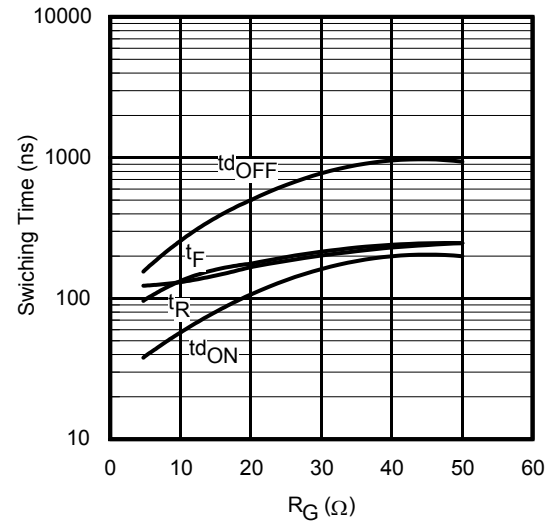
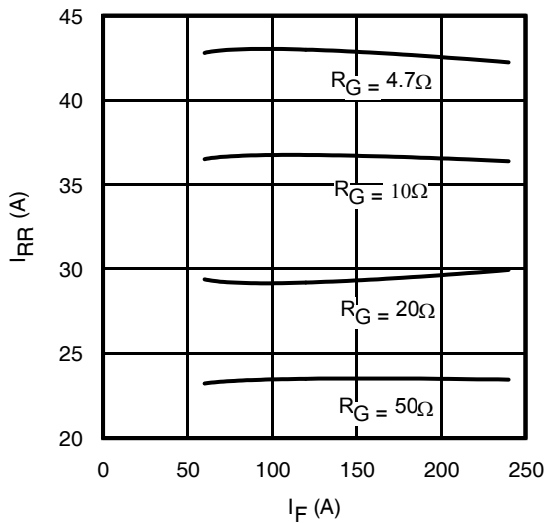
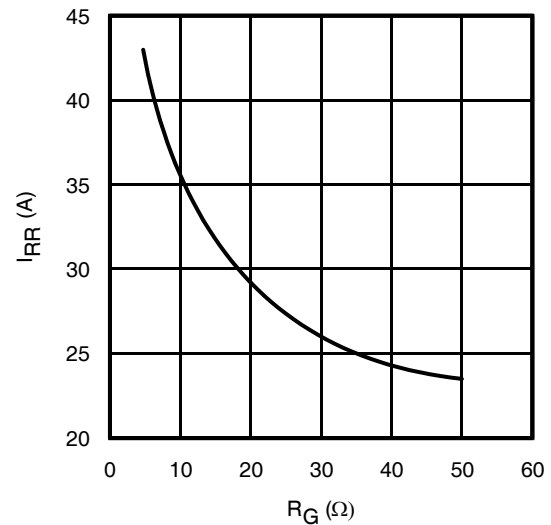


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 20\mu\text{s}$


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}; L = 0.087\text{mH}; V_{CE} = 400\text{V}; R_G = 4.7\Omega; V_{GE} = 15\text{V}$

Fig. 14 - Typ. Switching Loss vs. I_C
 $T_J = 175^\circ\text{C}; L = 0.087\text{mH}; V_{CE} = 400\text{V}; R_G = 4.7\Omega; V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}; L = 0.087\text{mH}; V_{CE} = 400\text{V}; I_{CE} = 120\text{A}; V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}; L = 0.087\text{mH}; V_{CE} = 400\text{V}; I_{CE} = 120\text{A}; V_{GE} = 15\text{V}$

Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

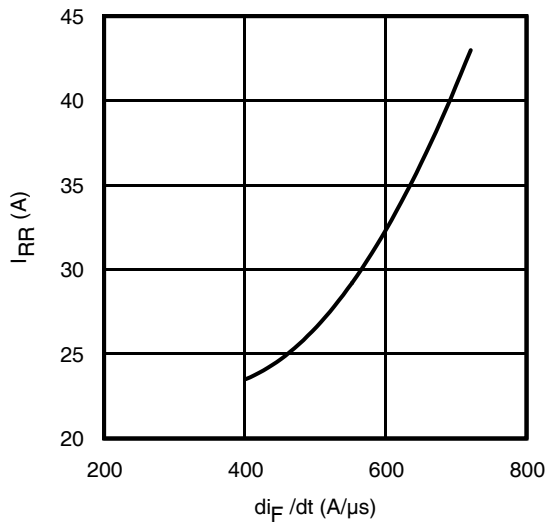


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 120A$; $T_J = 175^\circ C$

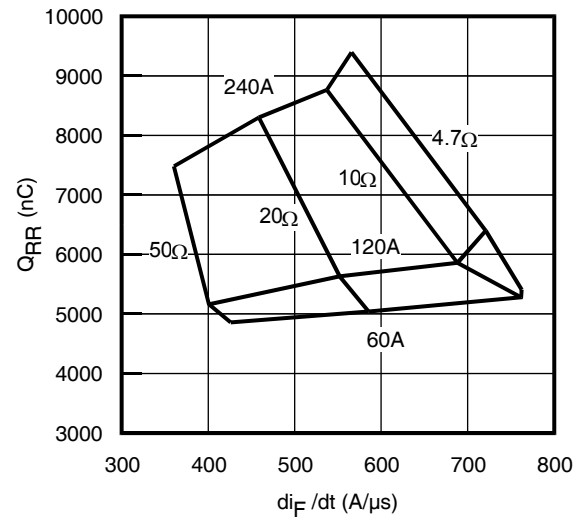


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

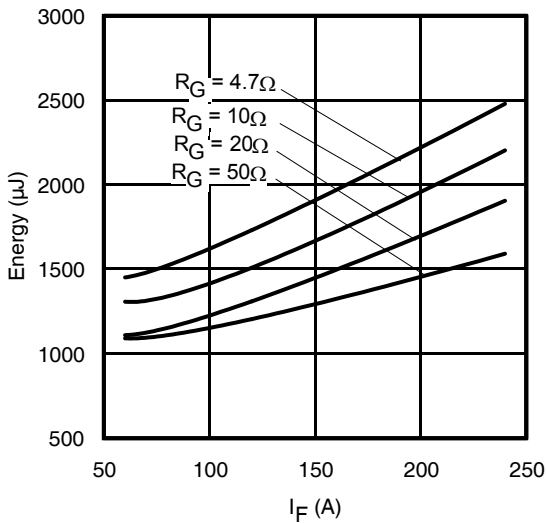


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

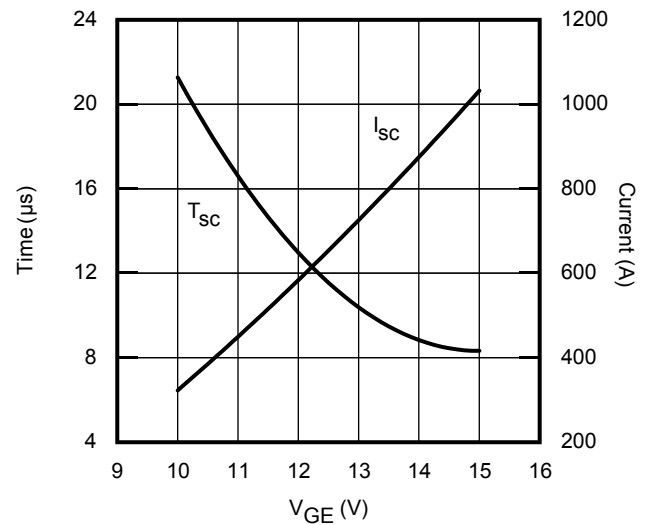


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

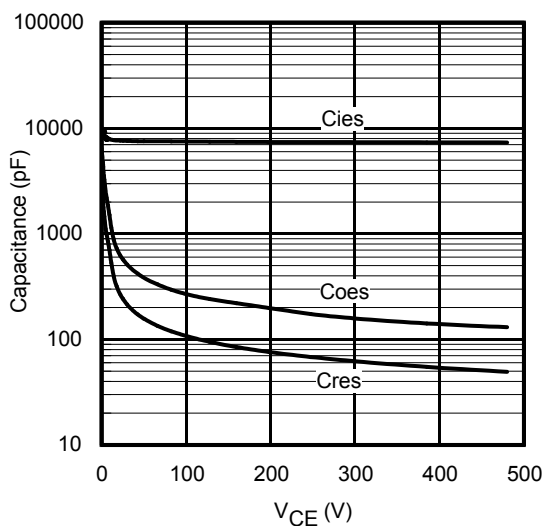


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

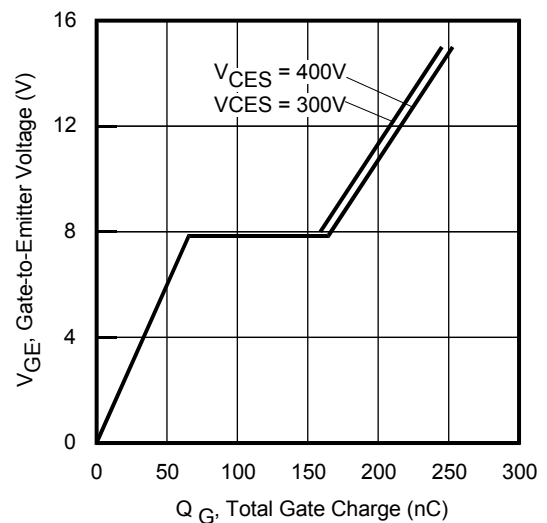
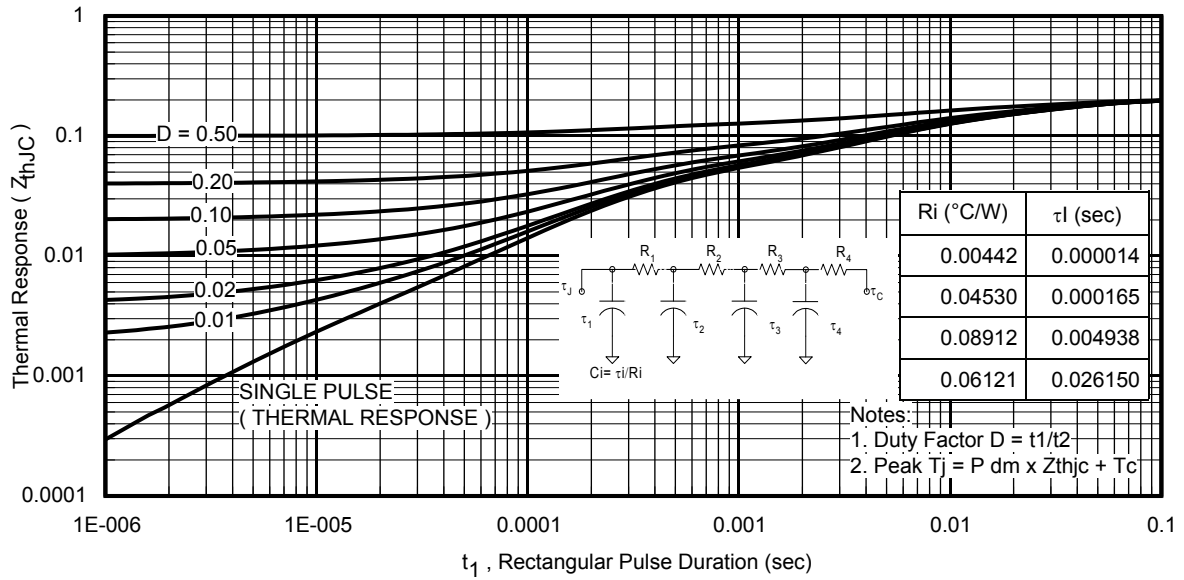
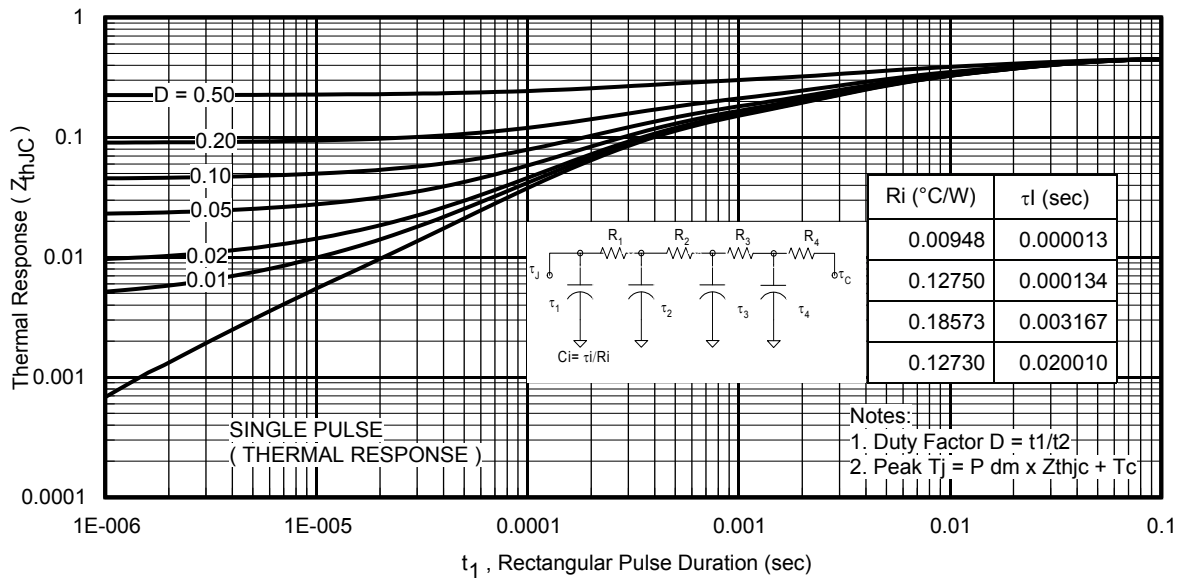
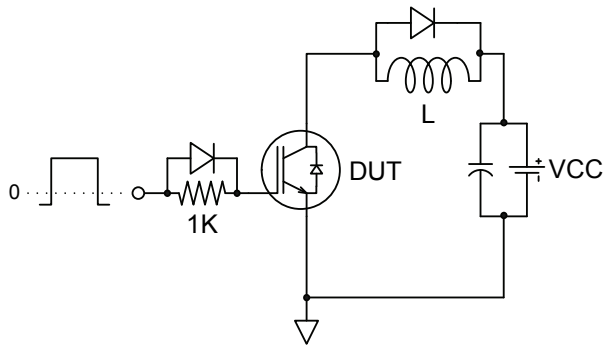


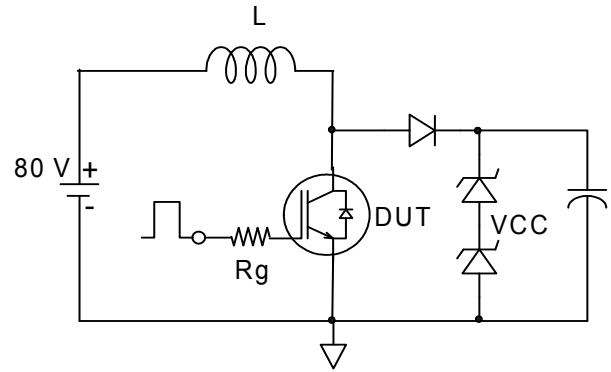
Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 120A$


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

Fig 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)



Gate Charge Circuit

Fig.C.T.1 - Gate Charge Circuit (turn-off)



RBSOA Circuit

Fig.C.T.2 - RBSOA Circuit

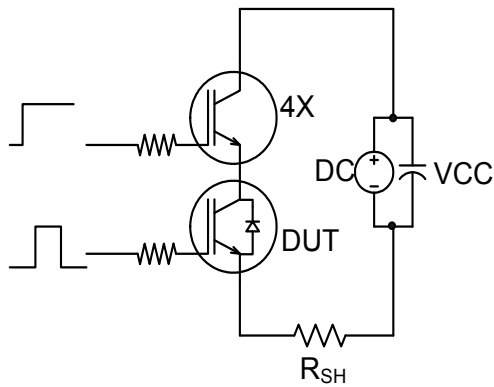


Fig.C.T.3 - S.C. SOA Circuit

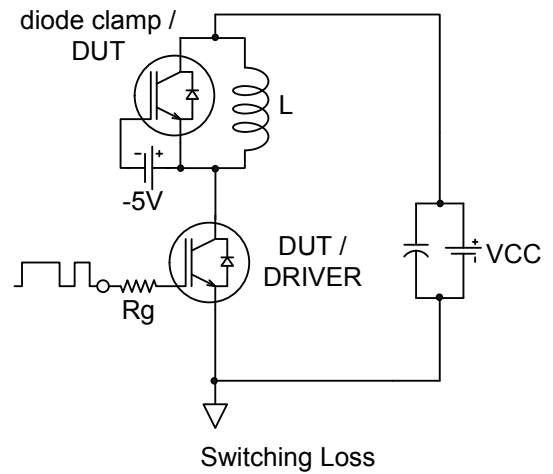


Fig.C.T.4 - Switching Loss Circuit

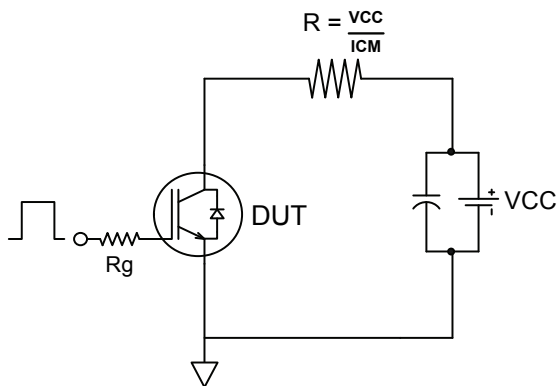


Fig.C.T.5 - Resistive Load Circuit

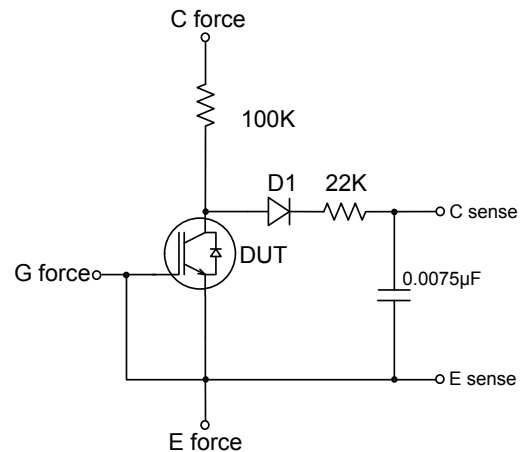


Fig.C.T.6 - BVCES Filter Circuit

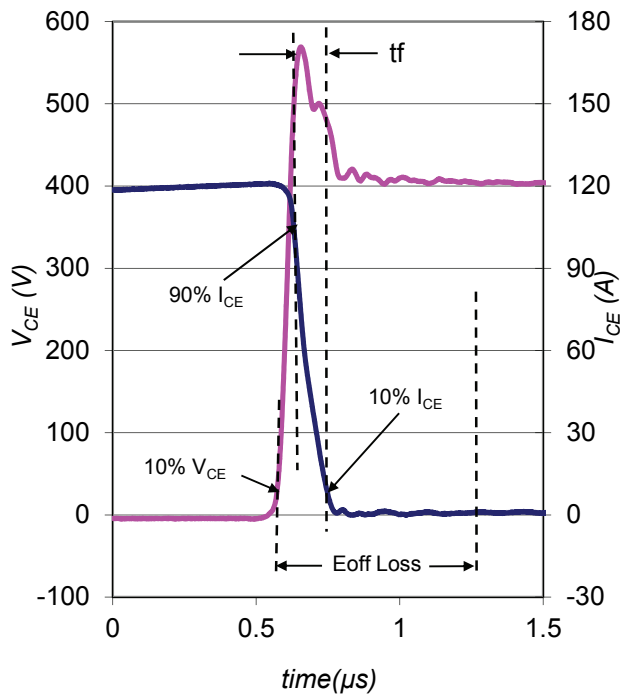


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

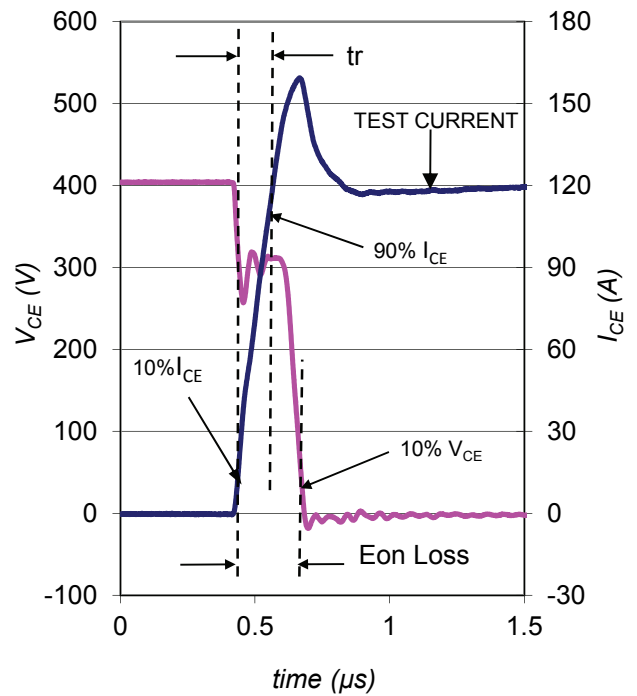


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

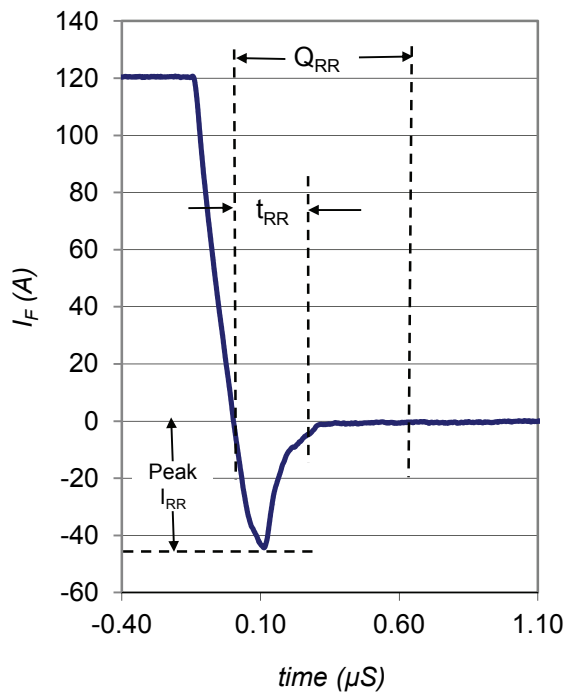


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

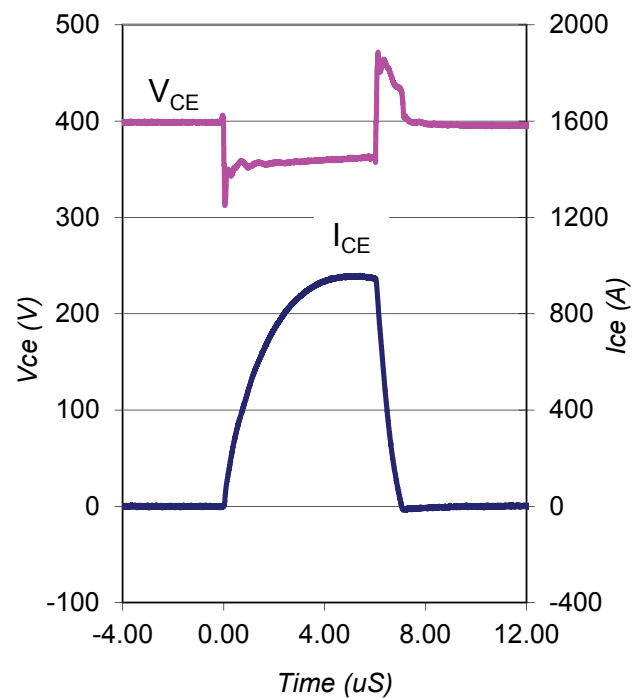
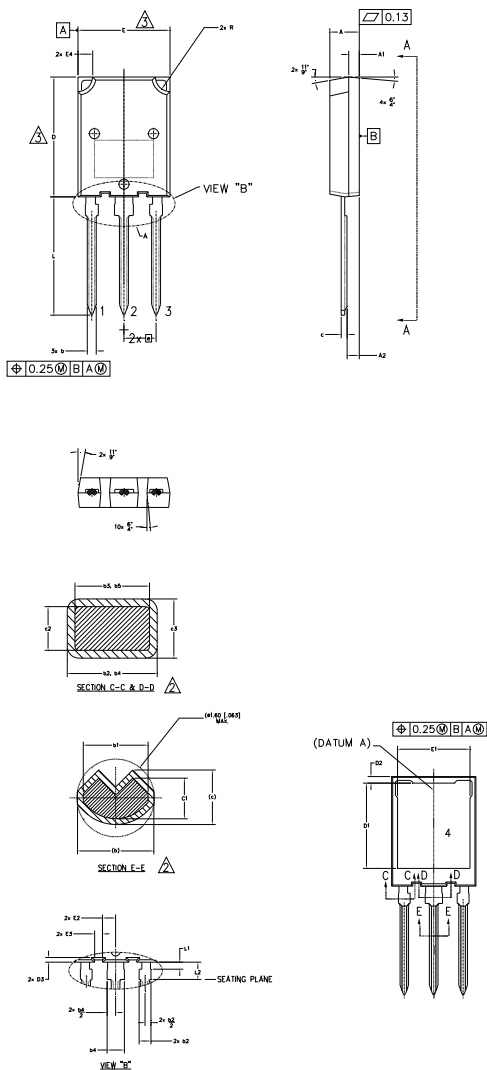


Fig. Wf4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

Case Outline and Dimensions-PG-TO274-3-903 (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS b1, b3, b5, c1 & c3 APPLY TO BASE METAL ONLY.
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
5. CONTROLLING DIMENSION: MILLIMETER.
6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-274AA

S Y M B O L	DIMENSIONS				N O T E S
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.90	5.10	.193	.201	
A1	1.70	2.10	.067	.083	
A2	1.88	2.13	.074	.084	
b	1.25	1.55	.049	.061	
b1	1.20	1.50	.047	.059	2
b2	2.00	2.30	.079	.091	
b3	1.92	2.22	.076	.087	2
b4	2.96	3.52	.116	.139	
b5	2.90	3.46	.114	.136	2
c	0.86	1.16	.034	.046	
c1	0.80	1.10	.031	.043	2
c2	0.65	0.85	.026	.033	
c3	0.50	0.70	.020	.028	2
D	20.16	20.44	.794	.805	3
D1	15.50	15.80	.610	.622	
D2	0.87	1.17	.034	.046	
D3	0.80	1.26	.031	.050	
E	15.20	15.80	.598	.622	3
E1	13.40	13.80	.528	.543	
E2	1.42	3.23	.056	.127	
E3	1.20	1.60	.047	.063	
E4	2.00	3.00	.079	.118	
e	5.45	BSC	.215	BSC	
L	19.72	20.38	.776	.802	
L1	1.10	1.50	.043	.059	
L2	2.85	3.61	.112	.142	
R	2.00	3.00	.079	.118	

LEAD ASSIGNMENTS

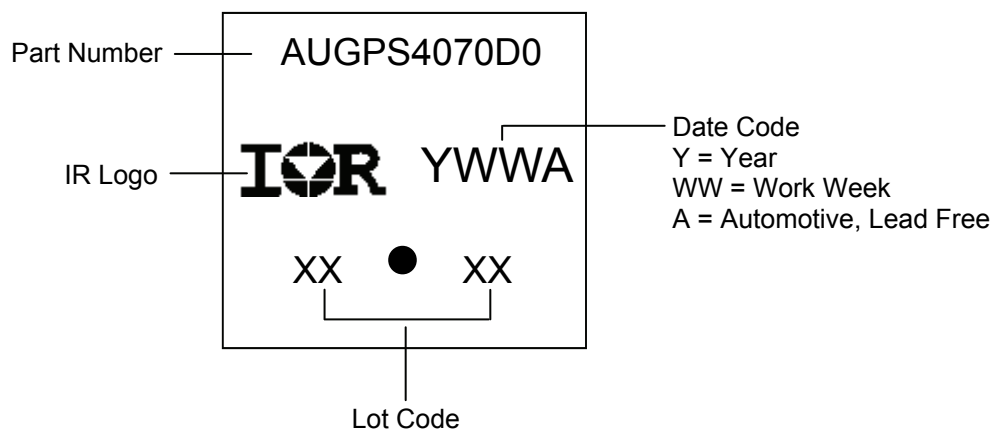
MOSFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

PG-TO274-3-903 -Part Marking Information



Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		PG-TO274-3-903	N/A
ESD	Human Body Model	Class H3B(+/- 8000) [†] AEC-Q101-001	
	Charged Device Model	Class C3 (+/- 2000) [†] AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Revision	Date	Subjects (major changes since last revision)
2.0	12/12/2016	• Final Datasheet.
2.1	08/31/2017	• Corrected typo error on part marking.
2.2	11/14/2017	• Updated with IFX nomenclature.
2.3	07/19/2018	• Updated with minor changes.
2.4	12/03/2018	• Updated with package outline.

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